



Modeling of Environmentally Friendly Siloxane-Based Lithography Solvents

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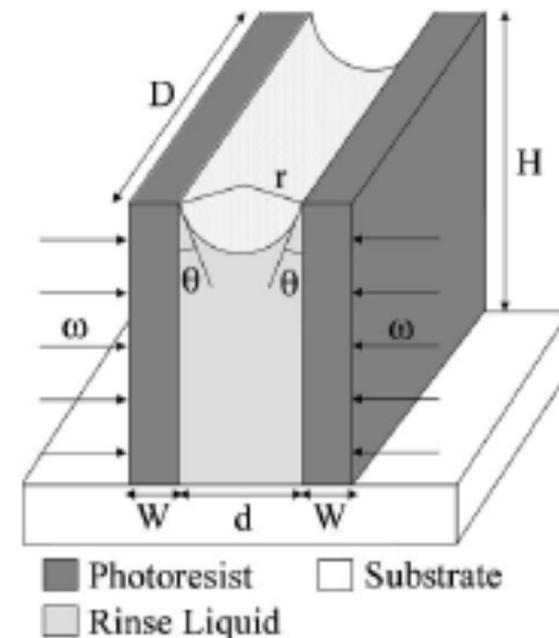
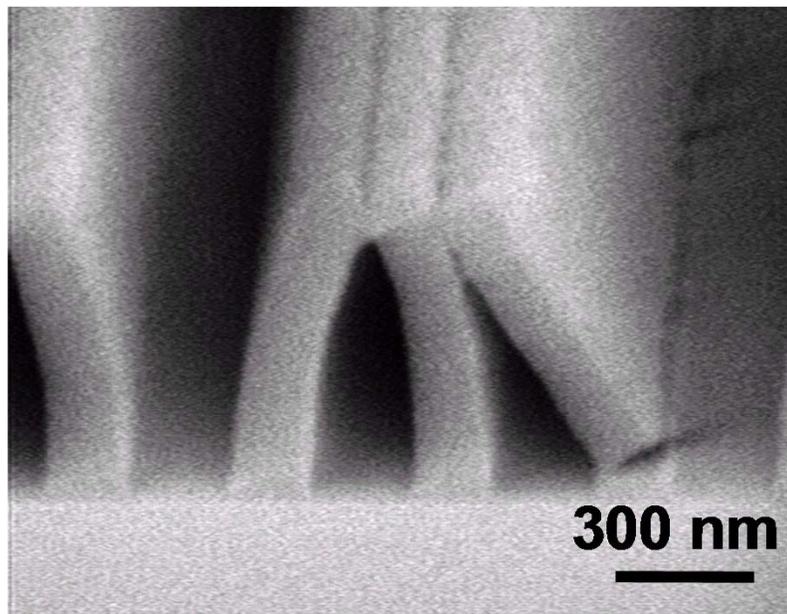
17 November 2011



Motivation



- Drive to reduce device dimensions has many obstacles remaining in its path.
 - Pattern collapse due to finite size effects and increased capillary forces during rinse
 - LER due to acid diffusion
 - Environmental concerns



Yoshimoto Stoykovich Cao, de Pablo, Nealey;
Journal of Applied Physics (2004)

Stoykovich, Cao, Yoshimoto, Ocola, Nealey, *Advanced Materials* **15** 1180 (2003)

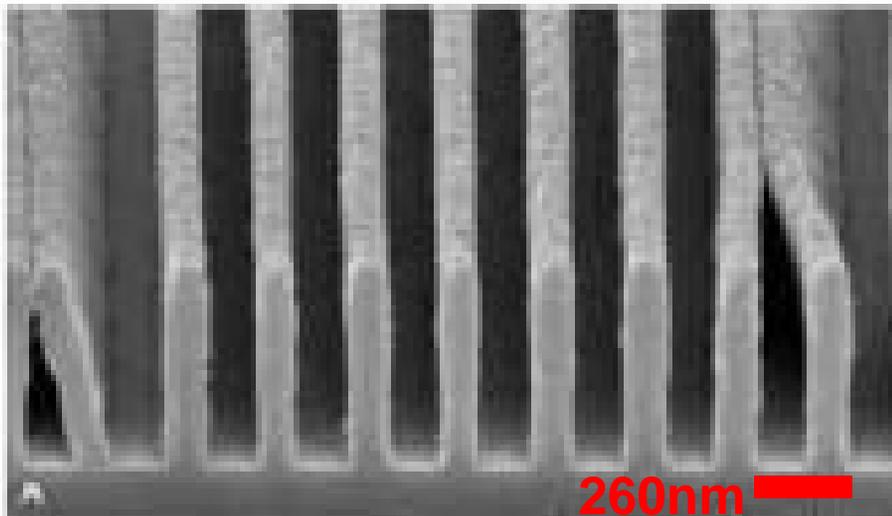


scCO₂ as a Solvent

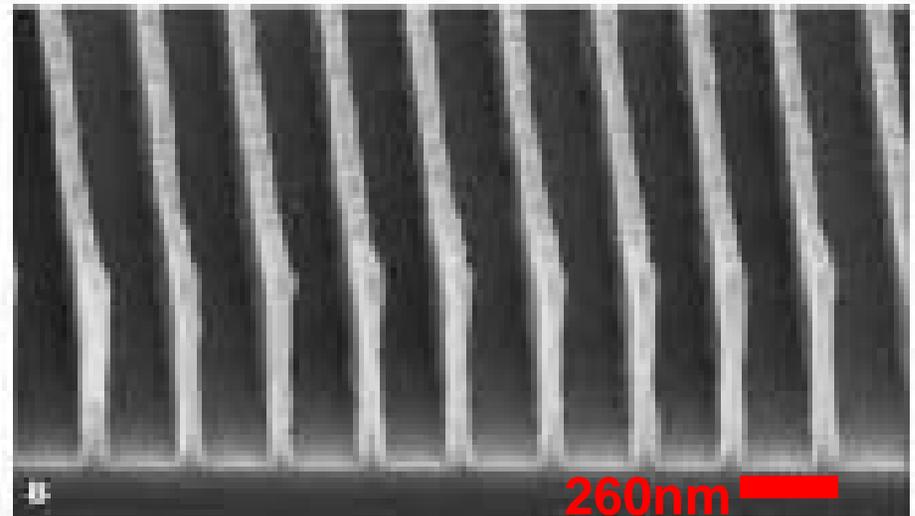


- No surface tension
 - reduced capillary forces => abates pattern collapse
- Plasticizes polymeric photoresist
 - reduced LER
- Requires additives to enhance resist solubility or new resists

Developed with TMAH, 122nm lines.



Developed with QAS/scCO₂, 42nm lines.



Wagner, DeYoung, Harbinson; SPIE Vol.6153 (2006)

Zweber, Wagner, DeYoung, Carbonell; Langmuir (2009)

Goldfarb, de Pablo, Nealey, Simons, Moreau, Angelopoulos (2000)



Objectives



- Environmental goals
- Methodology
- Super-critical carbon dioxide
 - Use with traditional photoresists
 - Use with molecular glass photoresists
- Linear methyl siloxanes
 - Benefits
 - Model development
 - Model validation
 - Use with traditional photoresists
 - Exploration of dissolution mechanism
- Future Work



ESH Metrics and Impact



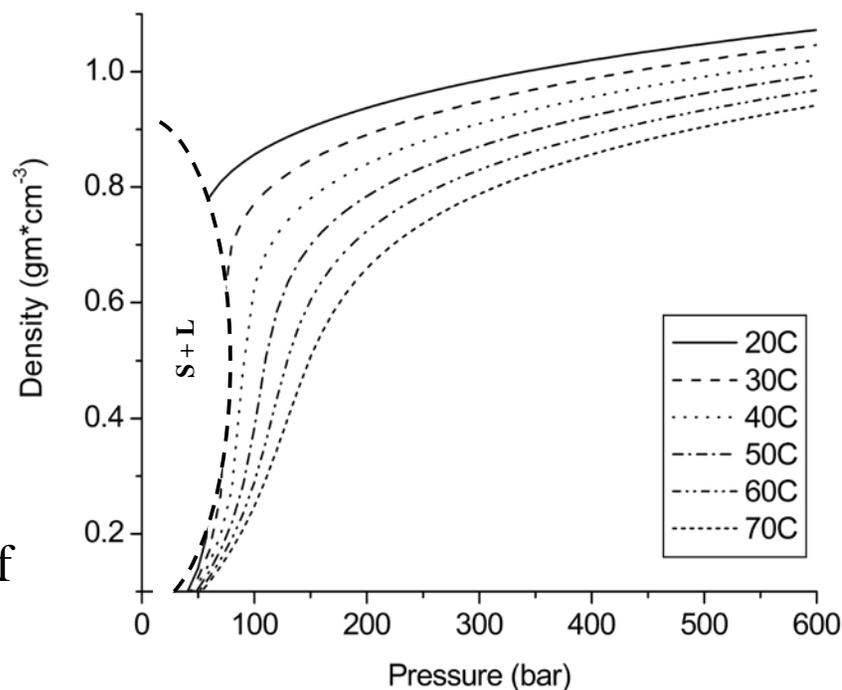
1. Reduction in the use or replacement of ESH-problematic materials
100% reduction in the use of aqueous base TMAH developer
2. Reduction in emission of ESH-problematic material to environment
Up to 100% reduction in VOCs and HAPs emission
3. Reduction in the use of natural resources (water and energy)
Eliminate water usage
Reduction in energy for water treatment and purification
4. Reduction in the use of chemicals
Minimal use of organic solvents



Why a Non-Aqueous Developer Solvent?



- Environmentally friendly, zero VOC solvent
- Highly tunable solvating power
 - $\rho(T,P)$
 - Leaves no residue
 - Clean separations
- One-phase fluid
 - Zero surface tension
 - Transport, viscosity between that of liquid and gas
- Nonpolar, inert character



Potential to reduce LER and eliminate pattern collapse

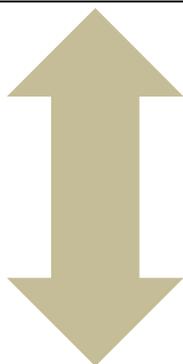


Collaboration



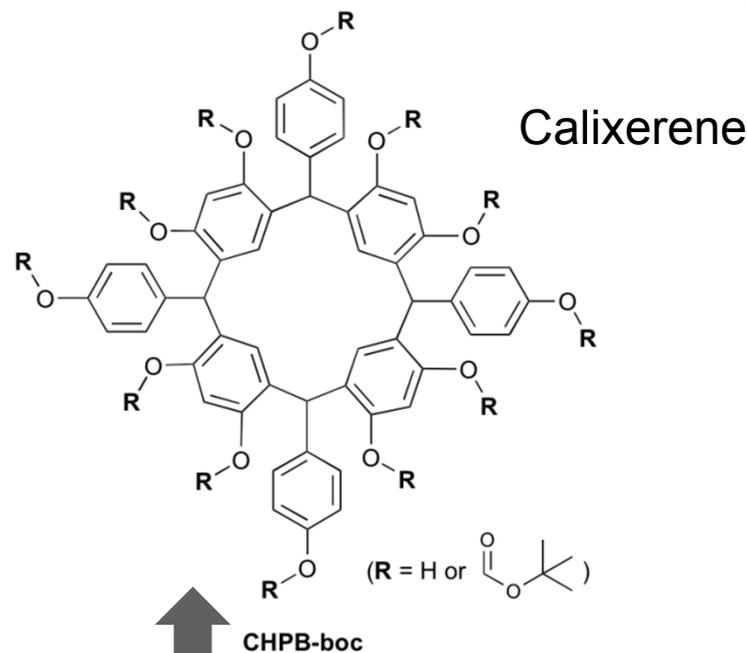
Ober Group

- Synthesize photoresists
- Development process
- Provide experimental results

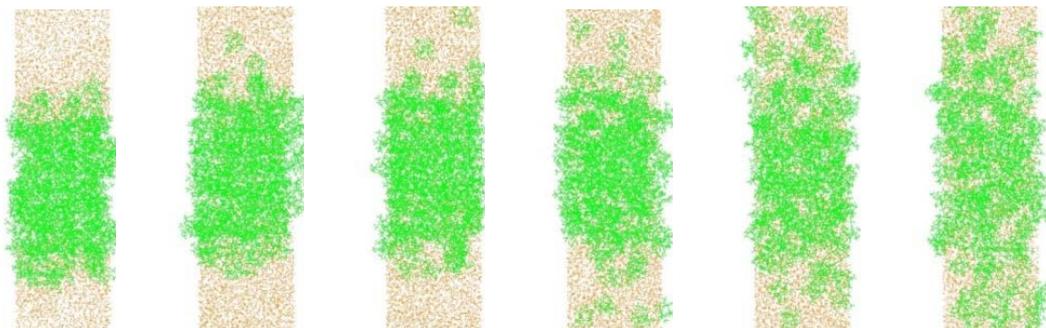


- Computer Simulations
- Pre-screening of possible photoresist structures
- Provide information on dissolution mechanism at a molecular level

de Pablo Group

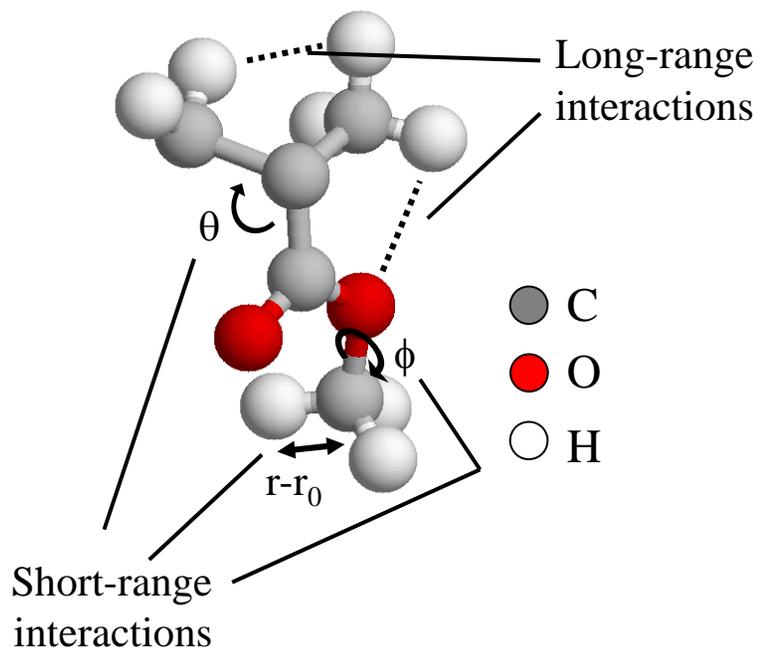


Time (1ns-2ns between images)



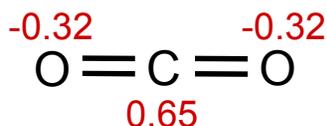


Model



OPLS Model:

$$V_{\text{tot}} = \underbrace{V_{\text{LJ}} + V_{\text{coul}}}_{\text{Intermolecular}} + \underbrace{V_{\text{bon}} + V_{\text{ang}} + V_{\text{tors}}}_{\text{Intramolecular}}$$
$$V_{\text{LJ}} = 4 \cdot \epsilon \cdot \left[\left(\frac{\sigma}{r} \right)^{12} - \left(\frac{\sigma}{r} \right)^6 \right]$$
$$V_{\text{coul}} = \frac{q_i \cdot q_j}{4 \cdot \epsilon_0 \cdot \epsilon \cdot r}$$
$$V_{\text{bon}} = \frac{1}{2} \cdot k_{\text{bon}} \cdot (r - r_0)^2$$
$$V_{\text{ang}} = \frac{1}{2} \cdot k_{\text{ang}} \cdot (\theta - \theta_0)^2$$
$$V_{\text{tors}} = \sum_n k_n \cdot (1 + \cos(n \cdot \phi - \phi_0))$$



- OPLS force field employed for most parameters
- We calculated charges (q_i) using quantum mechanics



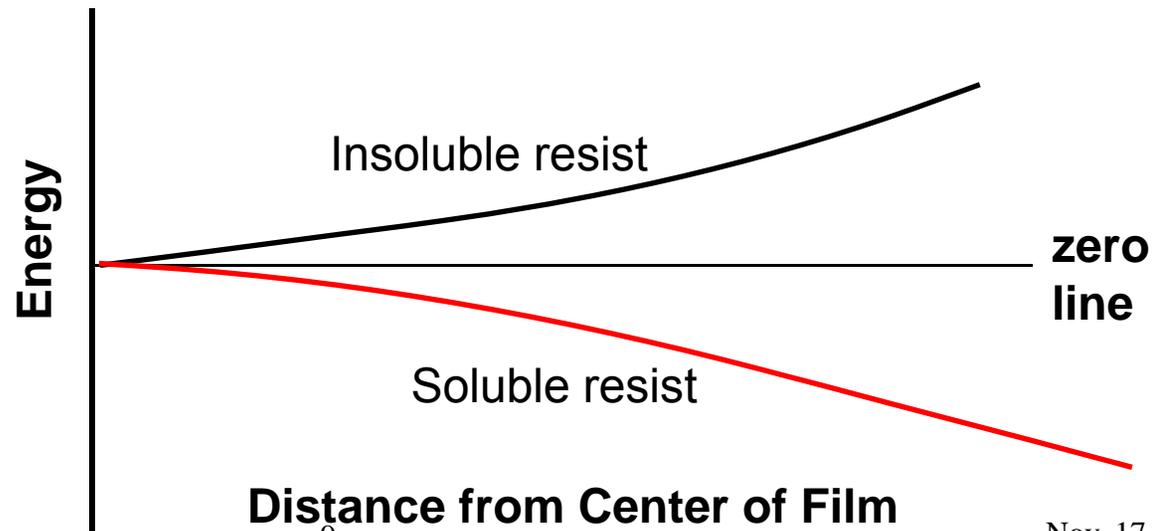
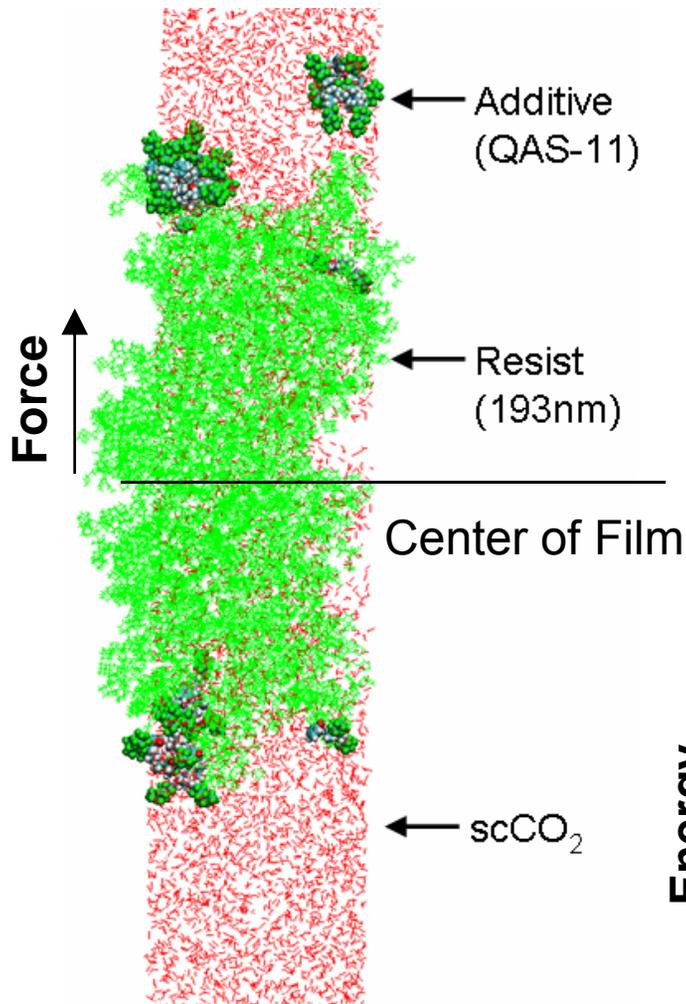
Film Energy Calculation



- Thin films of resist equilibrated in solvent via MD simulation
- Integrating the force on each chain as a function of position provide free energy

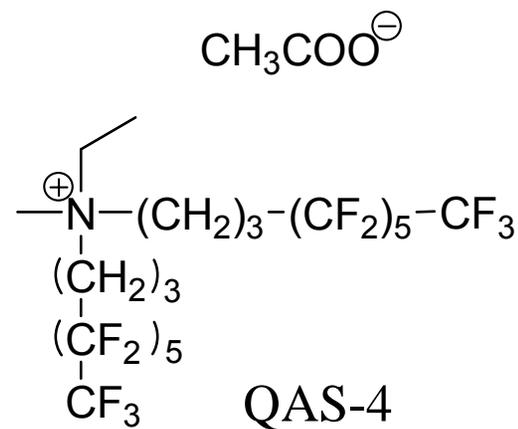
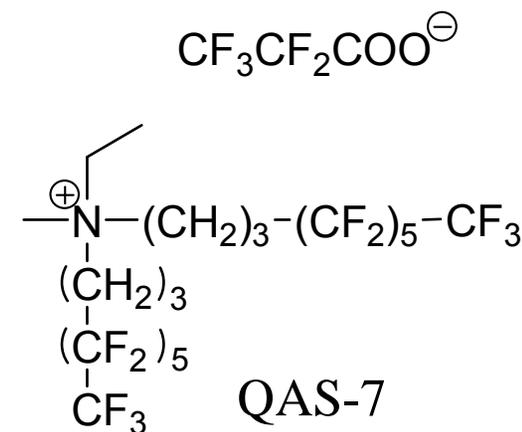
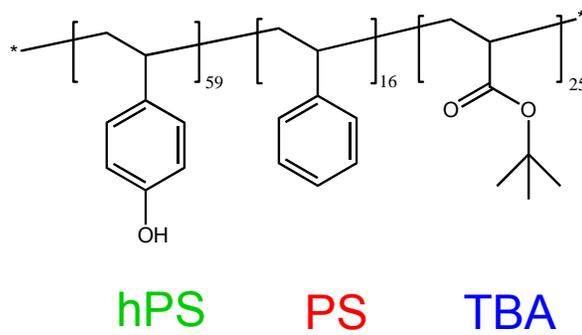
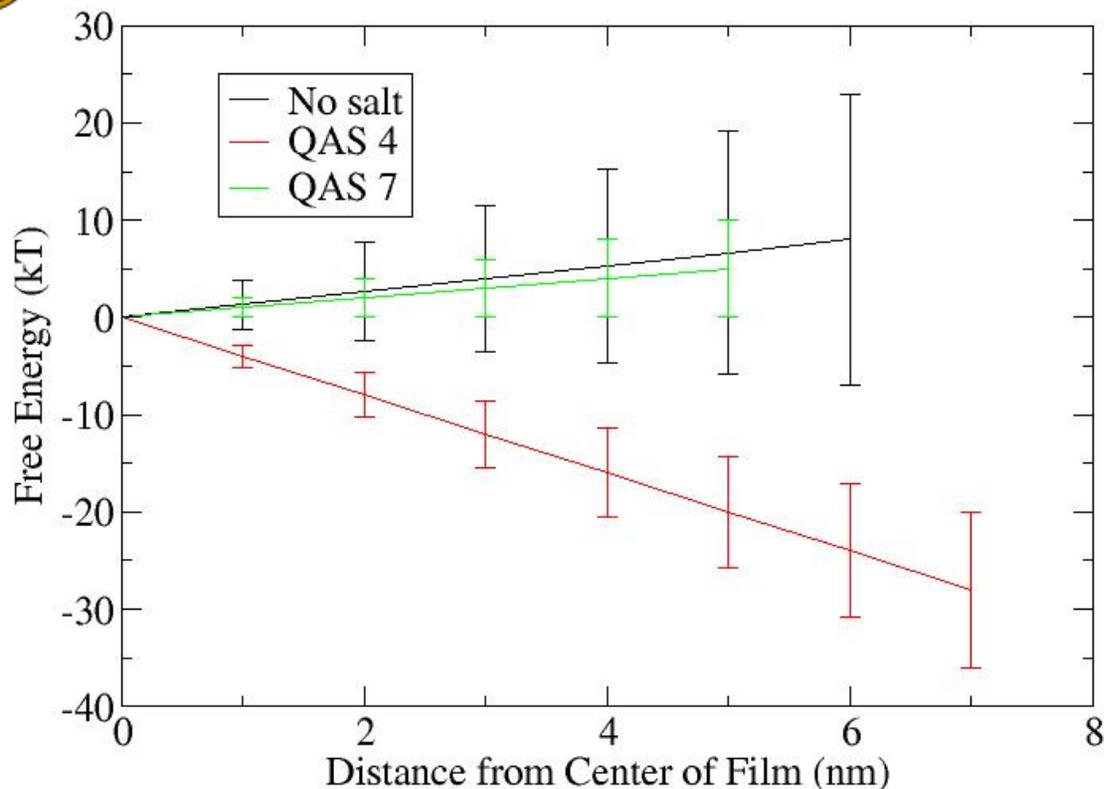
$$F(z) = \int_z^{z_\infty} \langle f(z') \rangle dz' + F(z_0)$$

- If the energy is lower at the surface than the center, the film is unstable



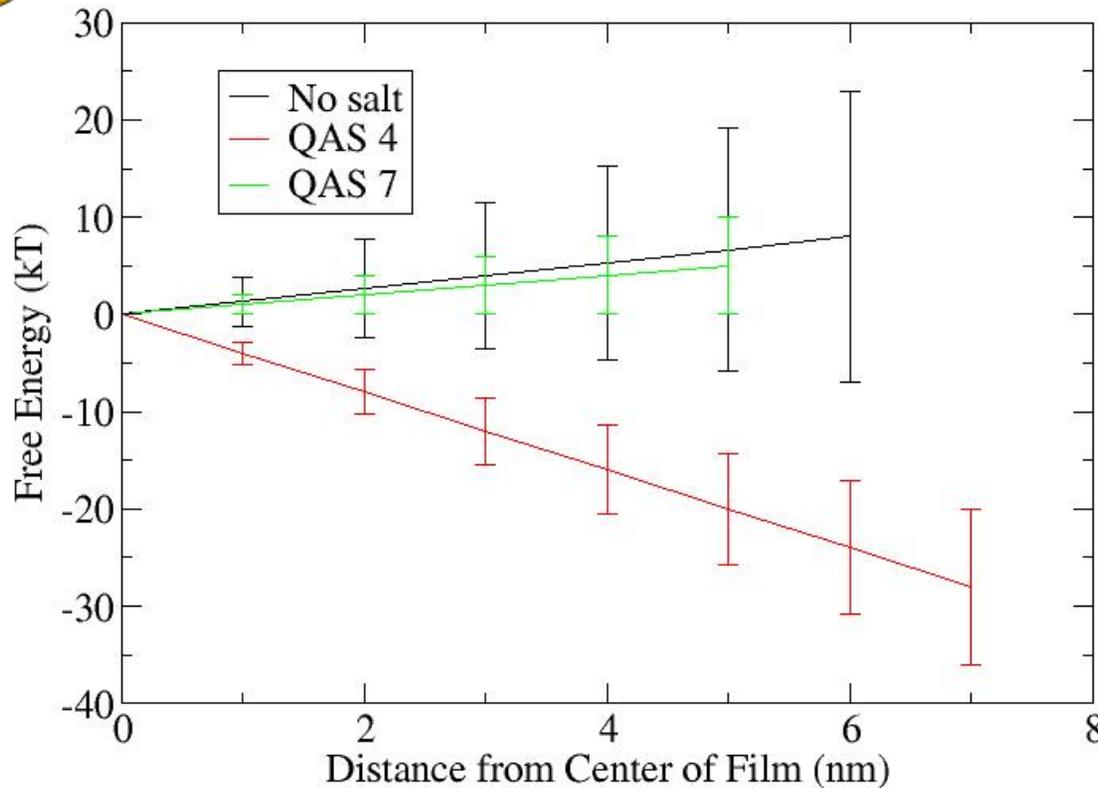


Sample Result: ESCAP Energy Curve





Sample Result: ESCAP Energy Curve



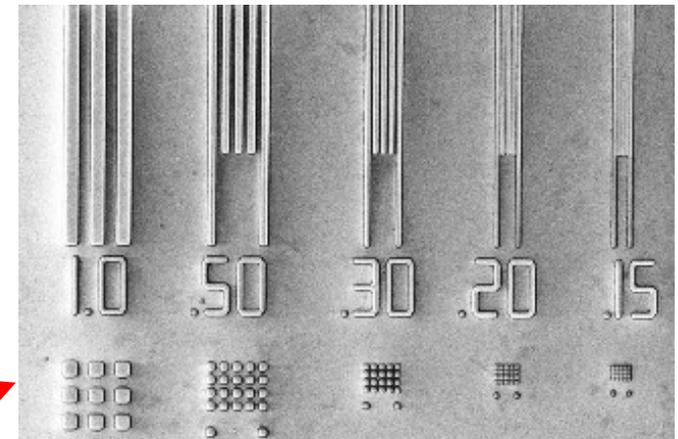
Experimental Results:

No salt – 0 nm/sec

QAS-7 – 0 nm/sec

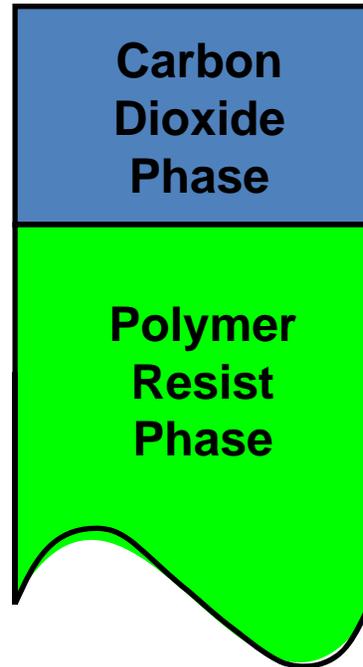
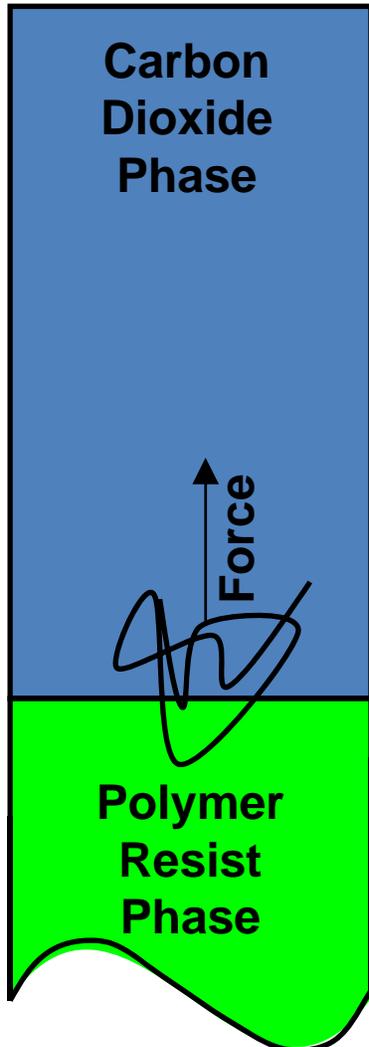
QAS-4 – 25 nm/sec

- Only addition of QAS4 to ESCAP results in reduced energy at surface of film (right of plot), indicating eventual dissolution
- Viability confirmed experimentally





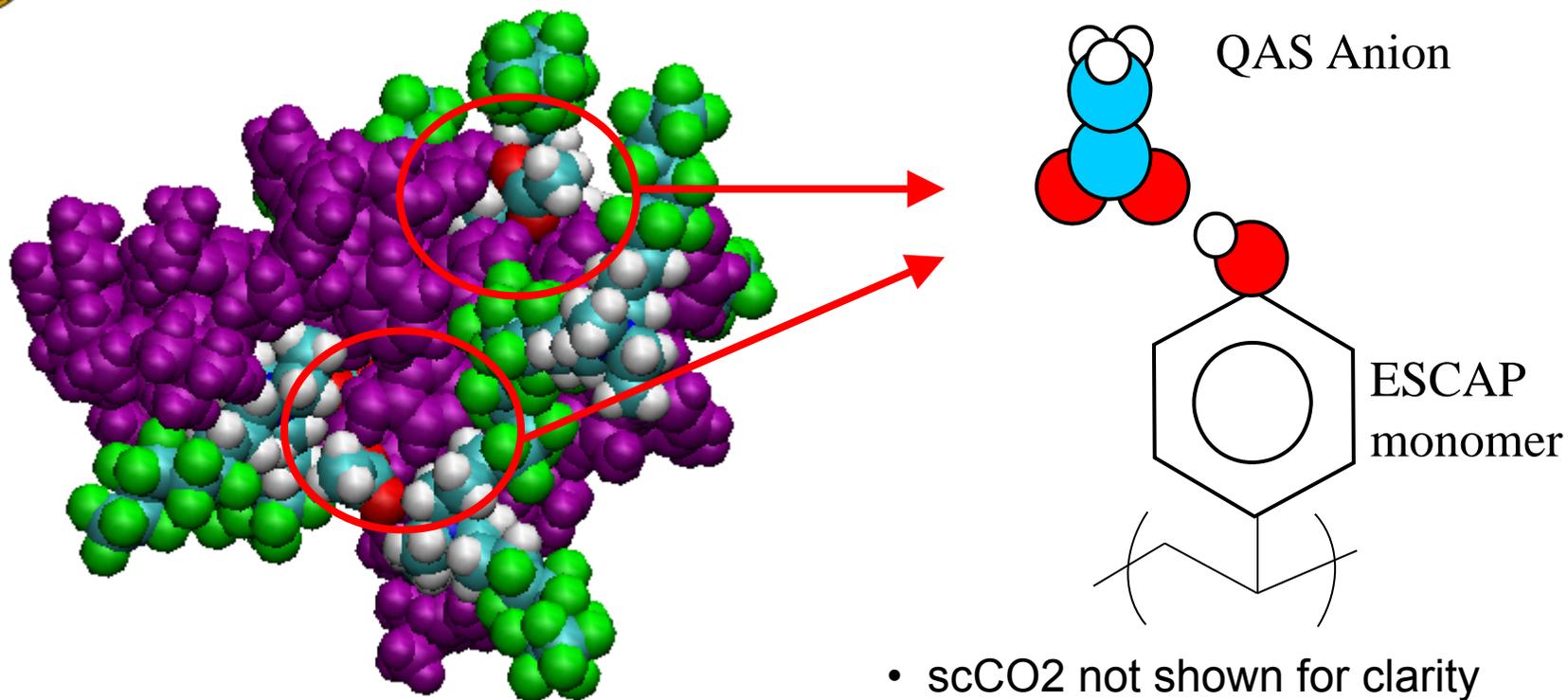
ESCAP Results



- scCO₂ not shown for clarity
- **Green** – ESCAP resist
- **Blue** – QAS-4
- **Cyan** – Carbon (Extracted Chain)
- **Red** – Oxygen (Extracted Chain)
- **White** – Hydrogen (Extracted Chain)



ESCAP Results



- The -OH group of ESCAP associates with the anions.
- Contacts last >500 ps.

- scCO_2 not shown for clarity
- **Purple** – ESCAP
- **Green** – Fluorine (QAS-4)
- **Cyan** – Carbon (QAS-4)
- **Red** – Oxygen (QAS-4)
- **White** – Hydrogen (QAS-4)



Comprehensive Understanding



- Examined polymer resist dissolution enhancement for both protected and unprotected resist
- Develop mechanistic understanding

PASS	Possible Pass	FAIL	Untested

Additive

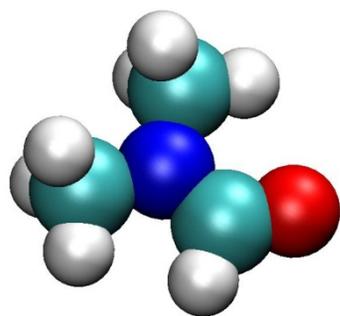
Photoresist	QAS4	QAS6	QAS7	QAS11	QAS12	QAS13	QAS14	Isocyanate	TMDS	HMDS	DMAA	PGMEA	Silane	DMTS	none
ESCAP															
193nm															
PHOST															
Calixarene															



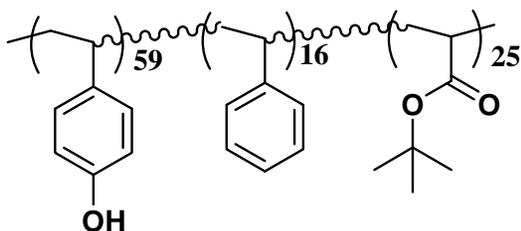
Additive Principles for DMAA



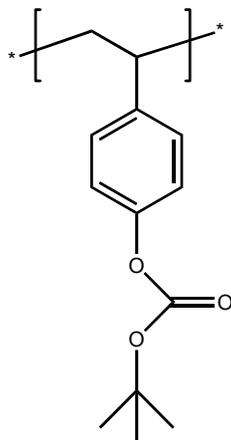
- QAS4 was effective due to hydrogen bonding; can we repeat this effect in a non-fluorinate additive?



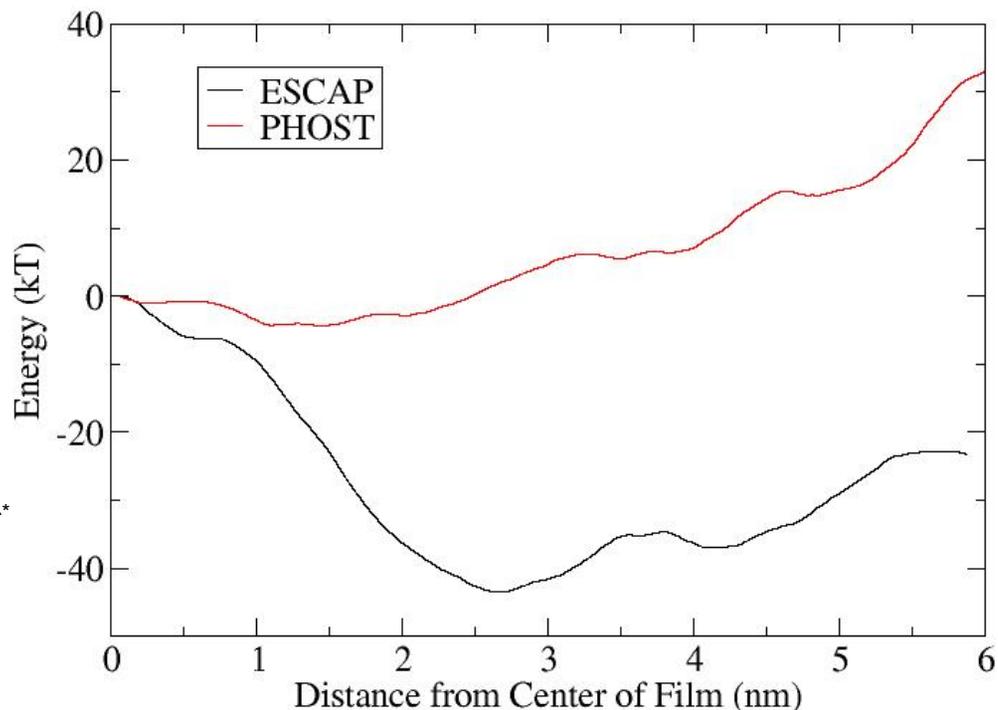
DMAA



ESCAP



PHOST



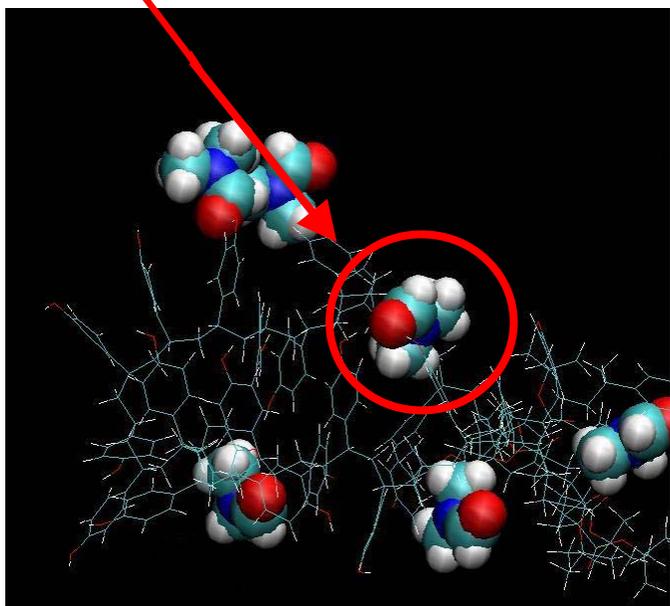
- DMAA enhances ESCAP solubility in $scCO_2$
- Unlike QAS4, does not aid PHOST development



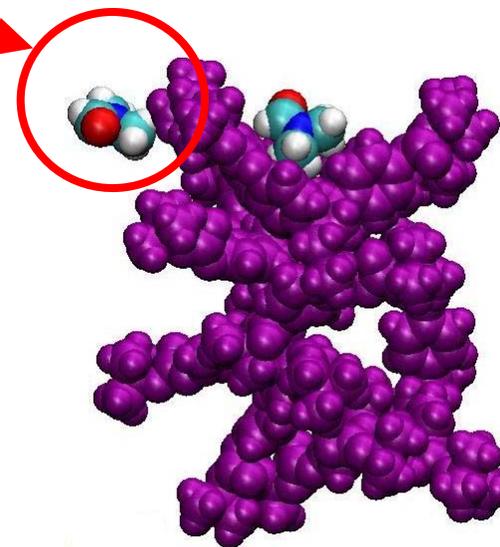
DMAA Mechanism



- Additive was based on applying our understanding of QAS4 effectiveness on ESCAP
- DMAA demonstrates similar hydrogen bonding
- Ineffective with PHOST; obstructs terminal t-butyl group, instead exposing polar region, reducing scCO₂ solubility



Can develop non-fluorinated additives, but they are more resist-specific

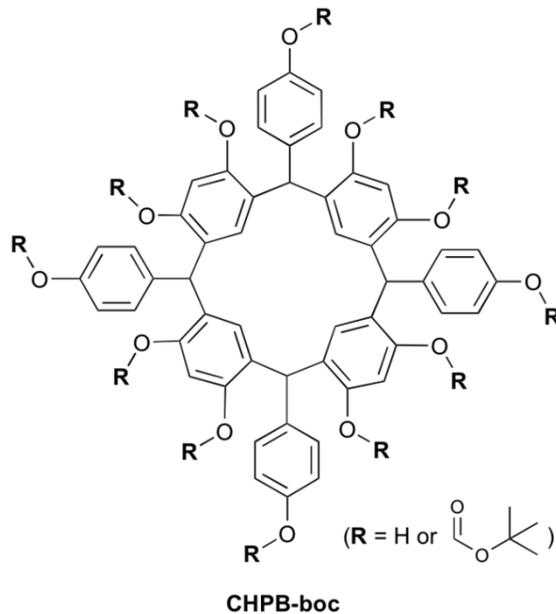




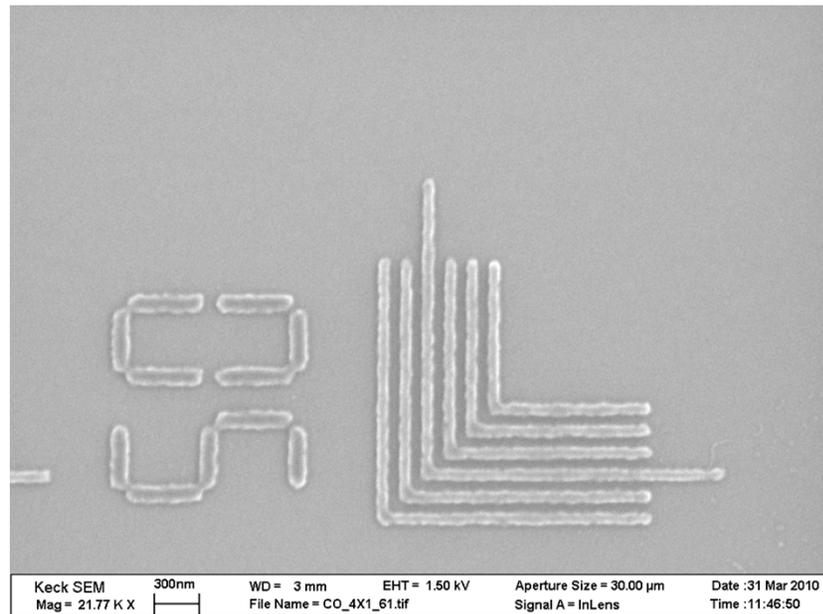
Molecular Glass Photoresist



- Low molecular weight materials capable of forming solid-like structures
- Improved LER
- More soluble than larger chemicals



Calixarene

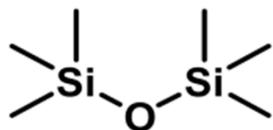




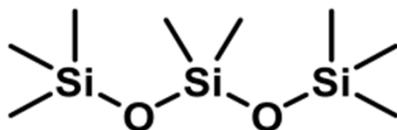
Silicon-Based Solvents



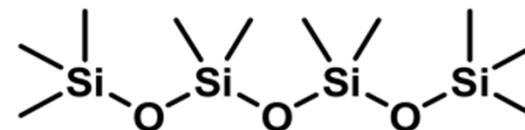
- Linear methyl siloxanes
- Low molecular weight
- Contain only silicon, carbon, hydrogen, and oxygen
- Non-polar solvent
- Solvent power can be enhanced by adding additives
- Low in toxicity, VOC exempt
- Non-ozone depleting
- Degrade to naturally occurring compounds
- Low surface tension



Hexamethyldisiloxane



Octamethyltrisiloxane



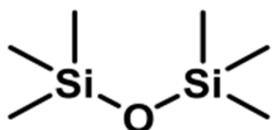
Decamethyltetrasiloxane



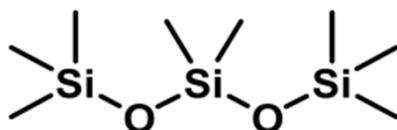
Objectives



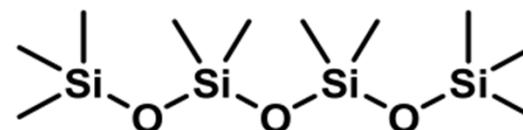
- Generate the definitive molecular model for siloxane solvents
 - Complete parameterization of all bonds, charges, etc.
 - Reproduction of experimentally-obtained chemical properties (density, heat of vaporization, etc.)
- Study behavior of traditional photoresists in siloxanes



Hexamethyldisiloxane



Octamethyltrisiloxane



Decamethyltetrasiloxane



Model

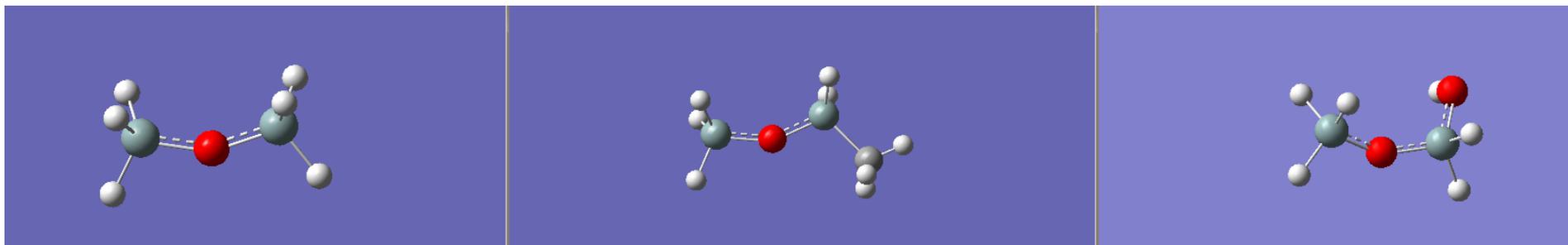


- Chose functional form consistent with generic formalism to enable transferability
- Parameters derived from quantum mechanical calculation and experimental analysis
- Modeled six elementary building blocks from which an arbitrary structure can be created

Model Formalism:

$$V_{Total} = \underbrace{V_{LJ} + V_{Coul}}_{\text{Intermolecular}} + \underbrace{V_{Bond} + V_{Ang} + V_{Tors}}_{\text{Intramolecular}}$$
$$V_{LJ} = 4\epsilon \left[\left(\frac{\sigma}{r} \right)^{12} - \left(\frac{\sigma}{r} \right)^6 \right]$$
$$V_{Coul} = \frac{q_i q_j}{4\epsilon_0 \epsilon r}$$
$$V_{Bond} = \frac{1}{2} k_{Bond} (r - r_0)^2$$
$$V_{Ang} = \frac{1}{2} k_{Ang} (\theta - \theta_0)^2$$
$$V_{Tors} = \sum_{n=0}^5 c_n \cdot \cos(\phi)^n$$

Sample elementary building blocks:



Si-O-Si-H

Si-O-Si-C

Si-O-Si-O

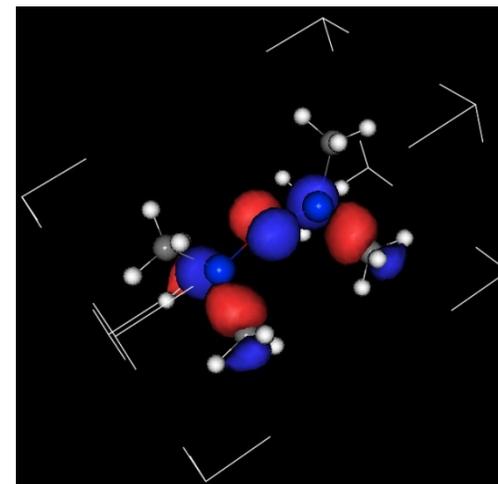


Quantum Mechanics



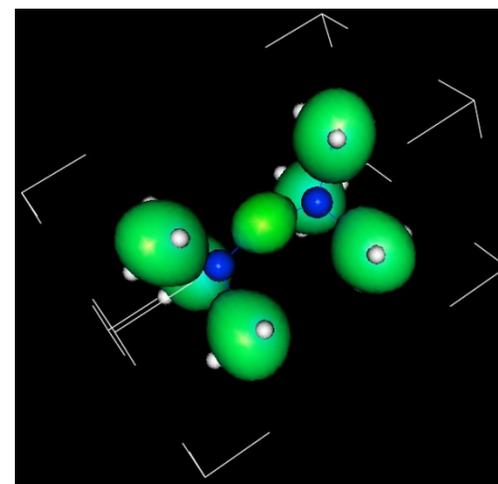
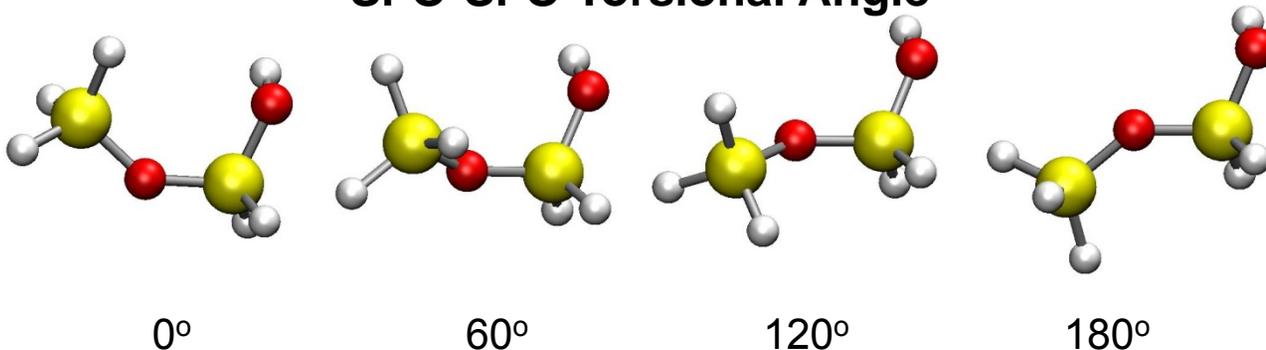
- Provides a detailed description of electron position as we probe different configurations
 - Can determine charges (q_i) directly
 - Map energy as a function torsion angle, etc.
 - rb3lyp model with 6-311+g(2d,p) basis set

HMD Siloxane



HOMO

Si-O-Si-O Torsional Angle



LUMO

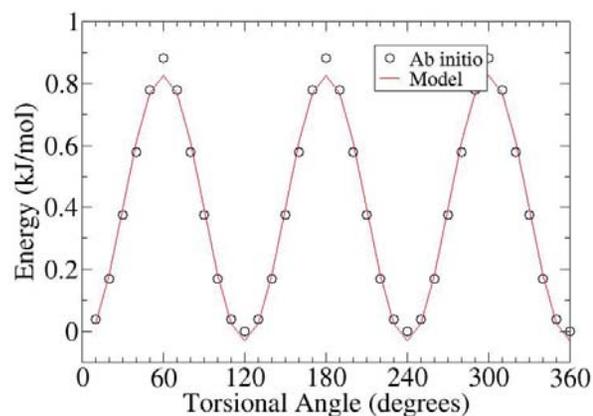


Potential Fitting – Torsional Sample

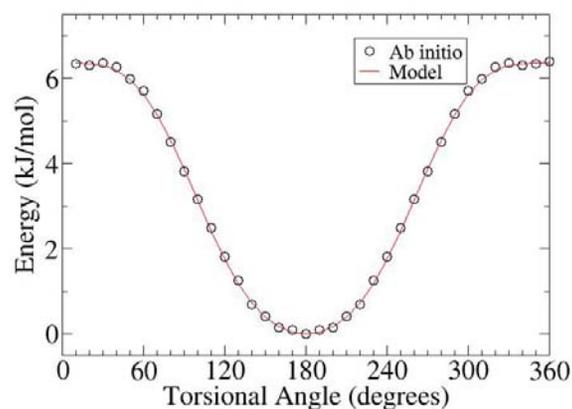


- Si-O-Si-C and Si-O-Si-O torsions most important parameters in determining shape of the solvents
- Torsional parameters fit to capture difference between quantum mechanical results and non-bonded interactions

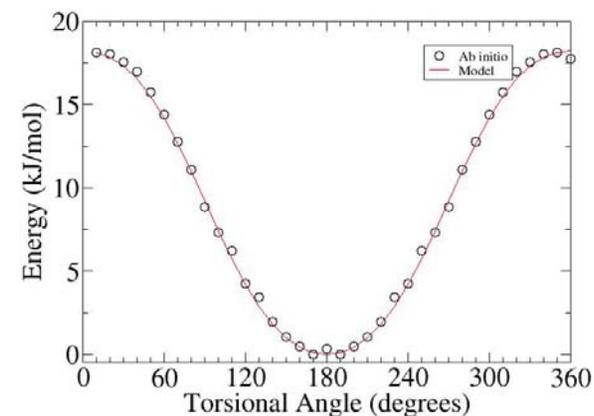
Si-O-Si-H



Si-O-Si-C



Si-O-Si-O

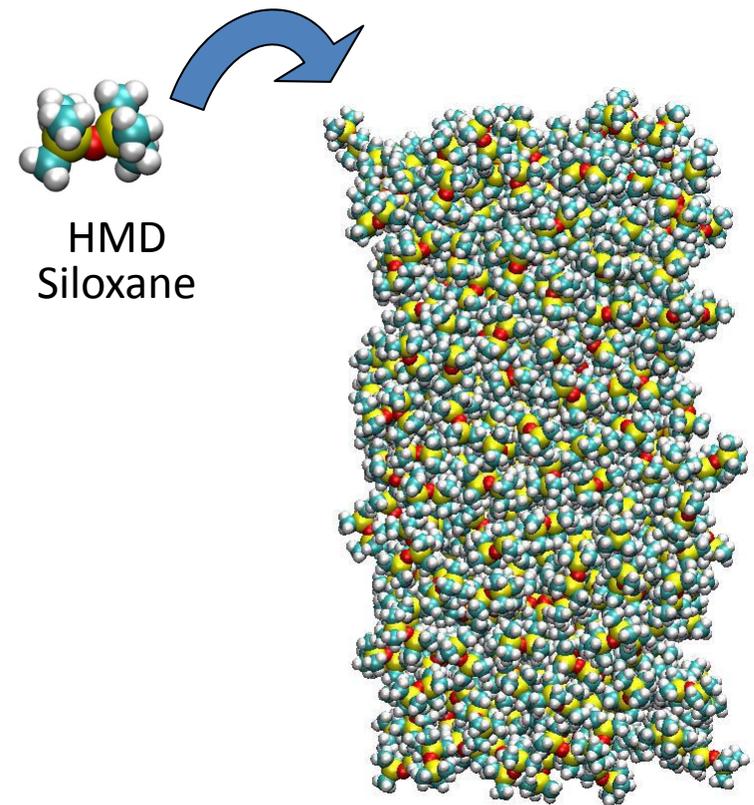
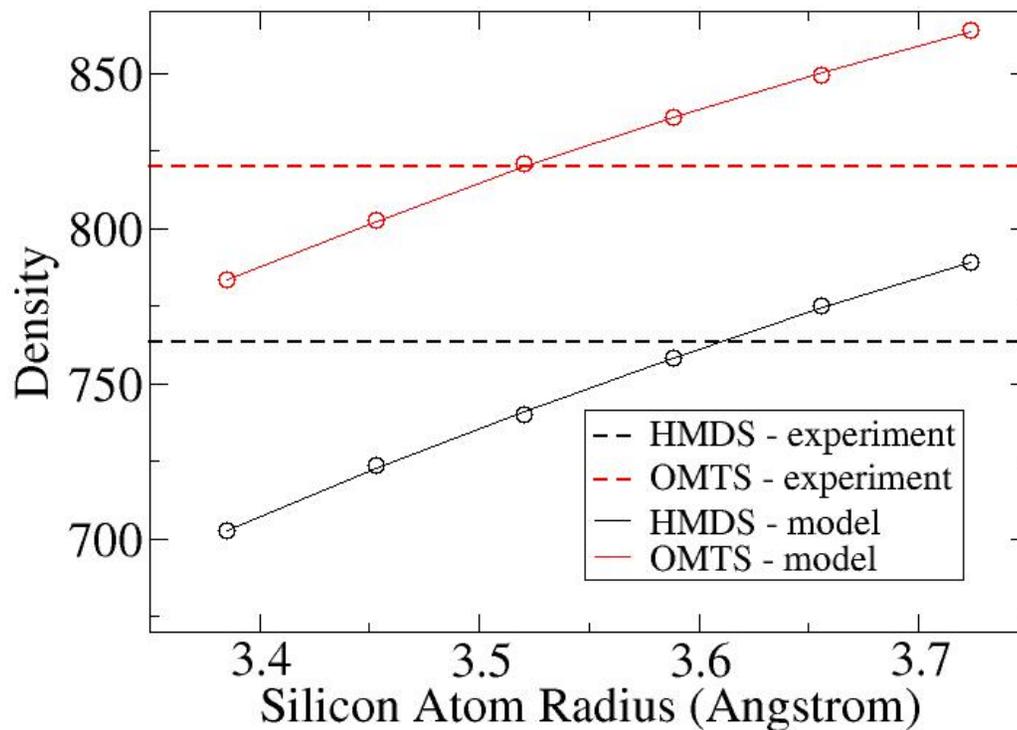




Intermolecular Interactions

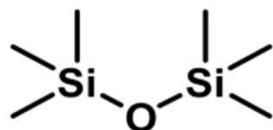


- Having built a complete intramolecular model from quantum mechanics, we now tune intermolecular many-body interactions to match experiment

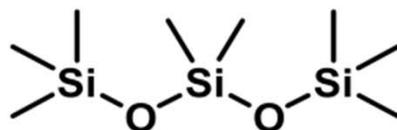




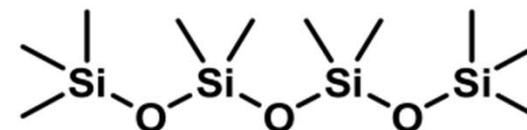
Model Verification



Hexamethyldisiloxane



Octamethyltrisiloxane



Decamethyltetrasiloxane

	HMD Siloxane		OMT Siloxane		DMT Siloxane	
	Experimental	Model	Experimental	Model	Experimental	Model
Heat of Vaporization (kcal/mol)	7.1	7.3	8.5	11.0	12.0	12.3
Specific Heat (cal/g*K)	0.46	0.50	0.29	0.48	0.41	0.53
Density (g/ml)	0.764	0.761	0.820	0.813	0.854	0.852
Dipole Moment (Debye)	Unknown	1.016	Unknown	1.203	Unknown	2.0553
Dielectric Constant	Unknown	1.339	Unknown	1.400	Unknown	1.875

- Good agreement with known properties



Energy Use



- Waste treatment is a major cost
 - Must separate solvent from dissolved polymer
- Siloxanes solvents require less heat to distill
 - Half the heat capacity
 - Order of magnitude lower heat of vaporization

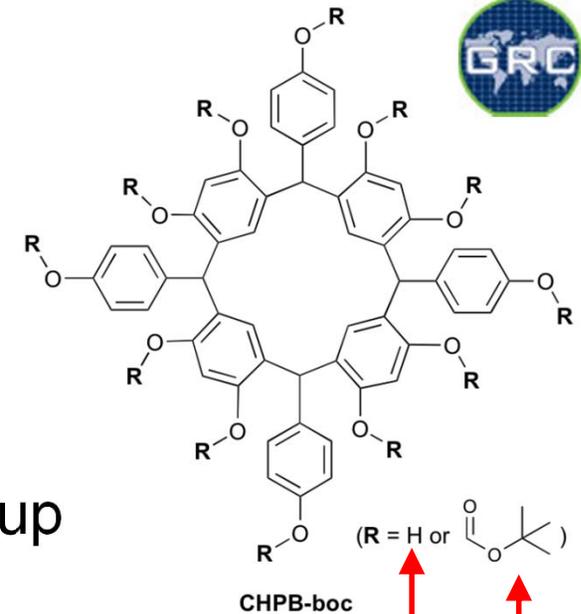
Solvent	TMAH	HMD Siloxane
C_p	3.2 - 4.18 J/g K	1.83 J/g K
T_{boil}	383K	373K
ΔH_{vap}	>2260 J/g	296 J/g



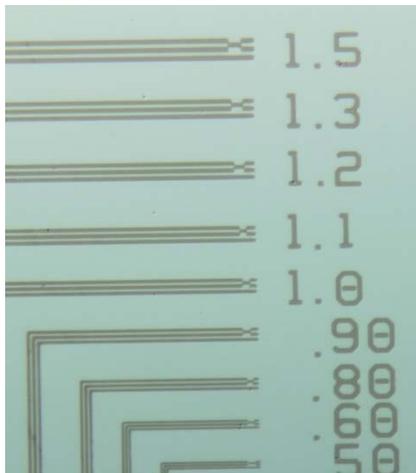
Calixarene



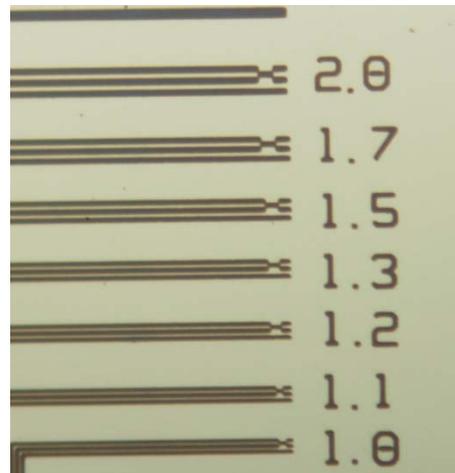
- Molecular glass resist
 - Inherently low LER
 - More soluble than polymers
- Selective dissolution proved by Ober group



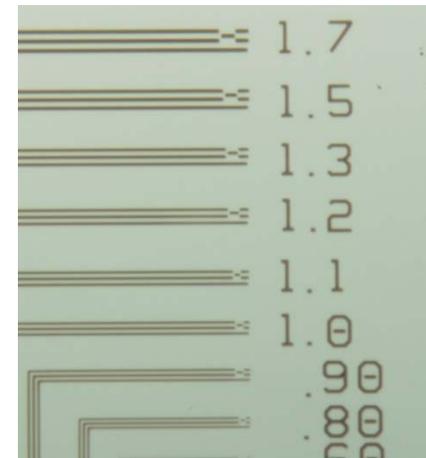
↑
exposed
↑
unexposed



HMD Siloxane
Dose: 350 mJ/cm²
PEB: 90°C, 30 sec



OMT Siloxane
Dose: 250 mJ/cm²
PEB: 90°C, 30 sec



DMT Siloxane
Dose: 300 mJ/cm²
PEB: 90°C, 30 sec

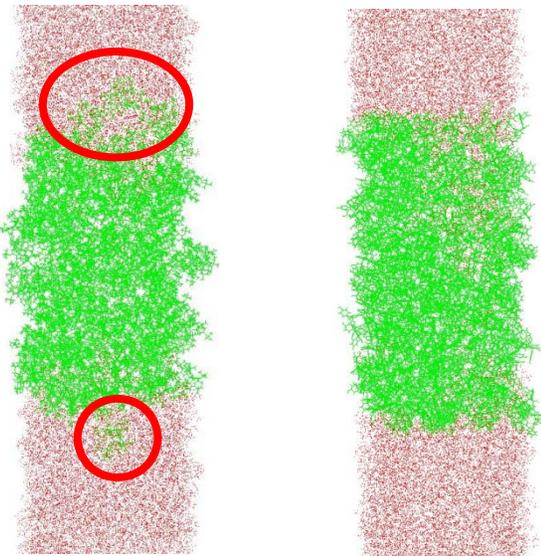


Calixarene Results

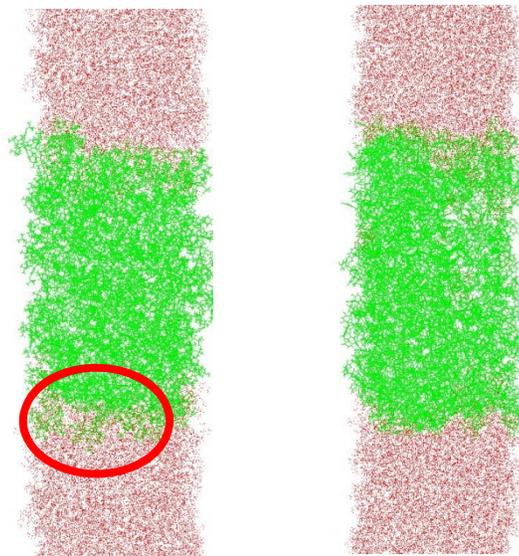


- Calixarene after 10ns in siloxane solvents:
 - Unexposed photoresist breaking away from surface
 - Exposed photoreist makes smooth interface
 - Negative tone resists
 - Excellent agreement with experiment

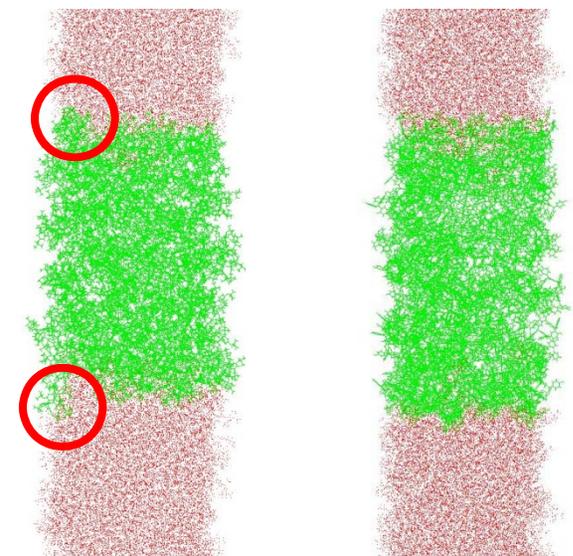
HMD Siloxane



OMT Siloxane



DMT Siloxane



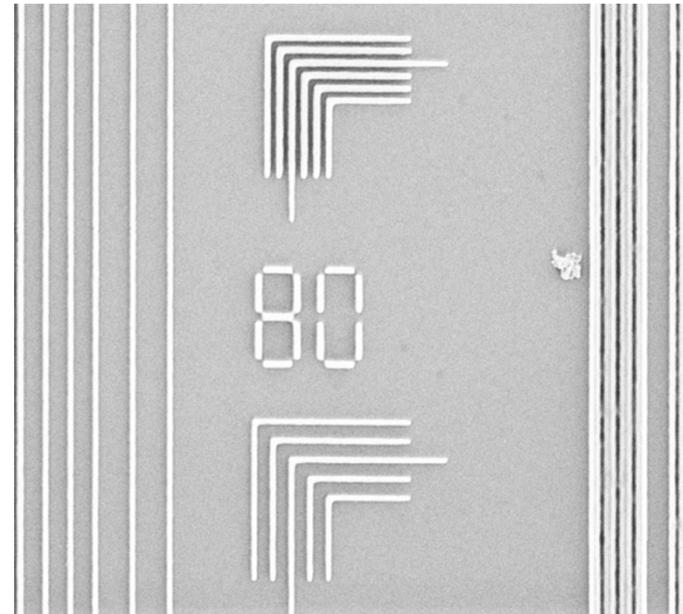
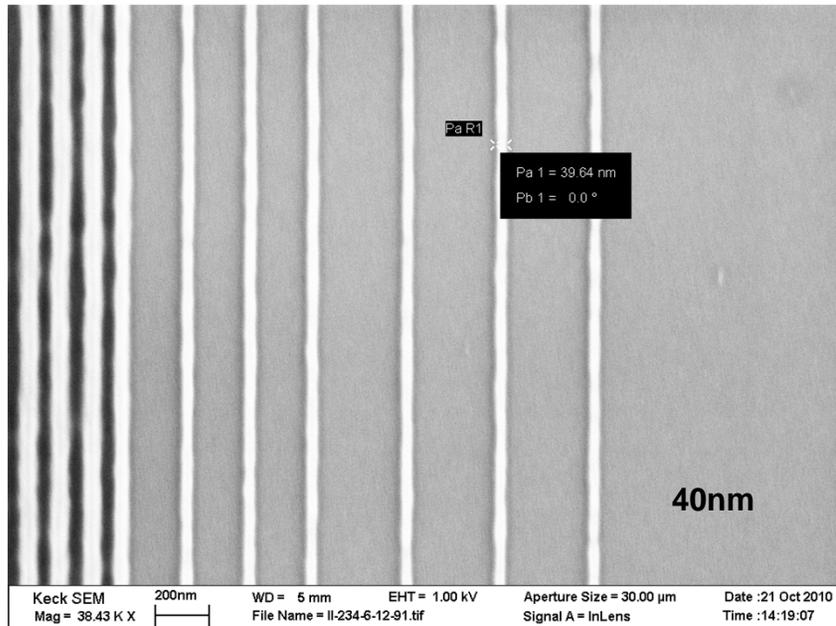
unexposed exposed

unexposed exposed

unexposed exposed



Calixarene Patterning



TOK photoresist
DMTS: HMDSO=1:20 at 40°C for 40 minutes
Resist film thickness ~350 nm

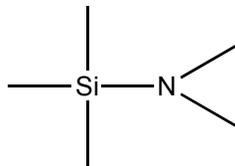


ESCAP



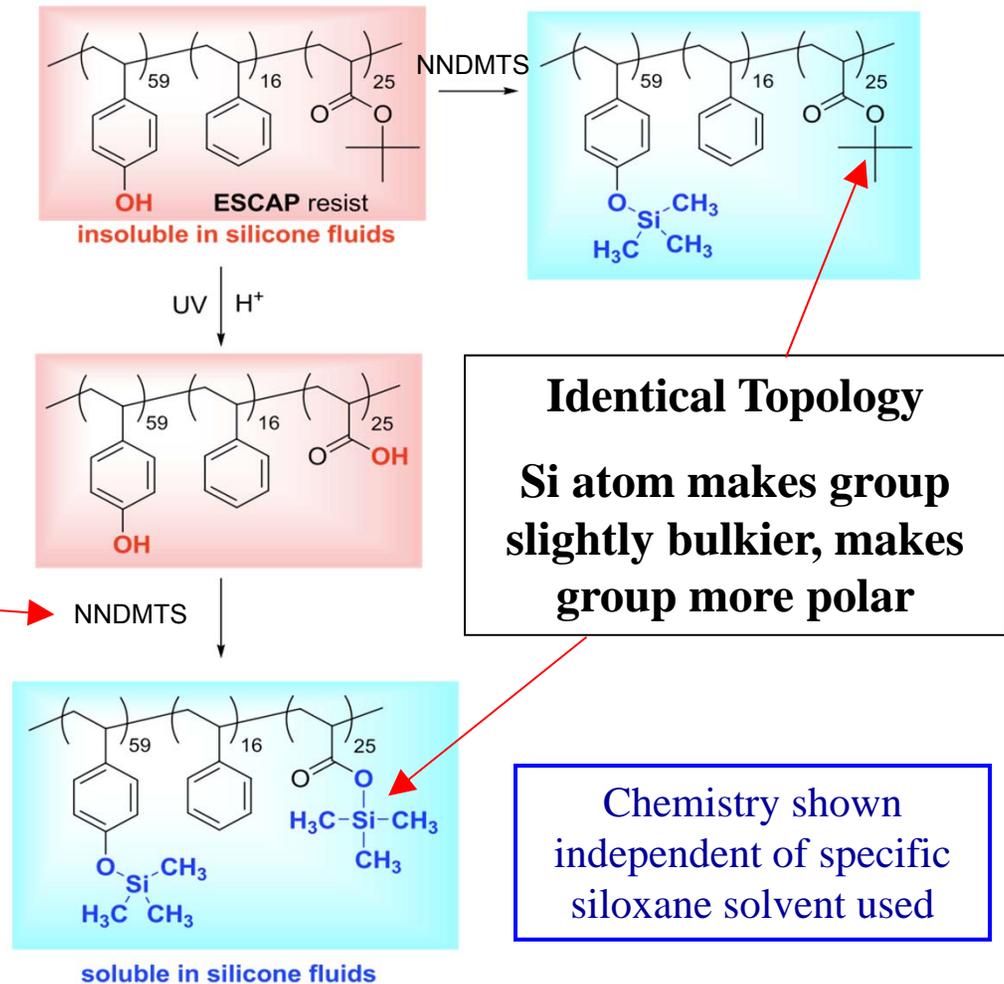
- ESCAP is our model EUV photoresist
 - Model previously developed and tested for $scCO_2$

- In experiment, chemically modified by NNDMTS:



(N,N-Dimethyl)trimethyl silane

- Similarity between exposed and unexposed form makes ESCAP a serious test of model sensitivity

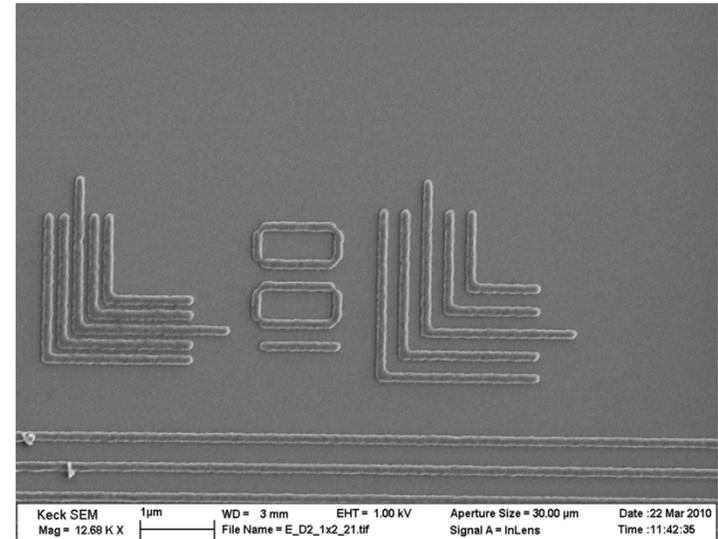
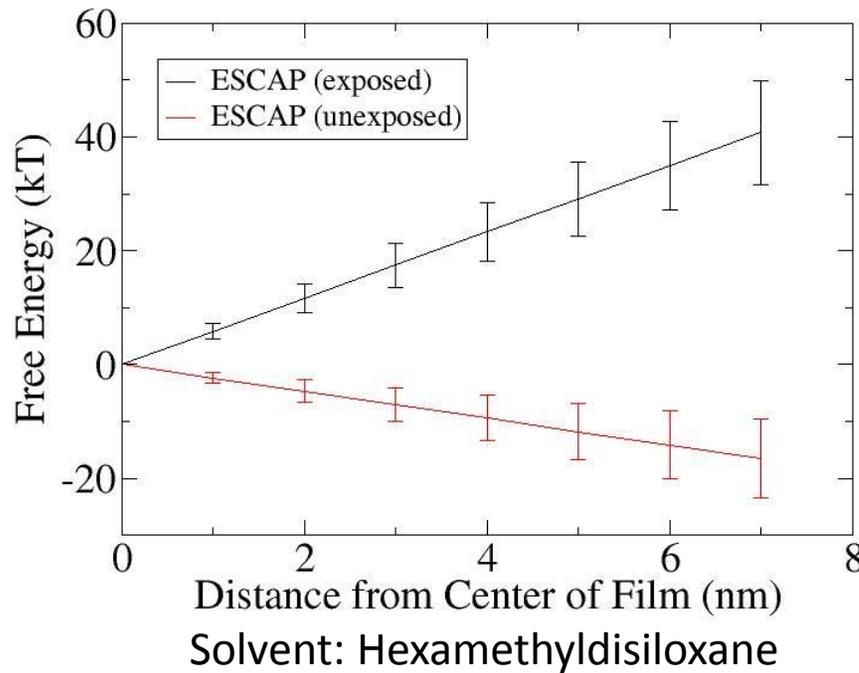




ESCAP Results



- Model predicts only unexposed films to be unstable:
 - Negative Tone
- Results from experimental collaborator corroborate result



Solvent: DMTS/Decamethyltetrasiloxane

e-beam dose = $20 \mu\text{C}/\text{cm}^2$

Photoresist: ESCAP

Chemical modifier: NNDMTS

Solvent: Decamethyltetrasiloxane

Dose = $20 \mu\text{C}/\text{cm}^2$

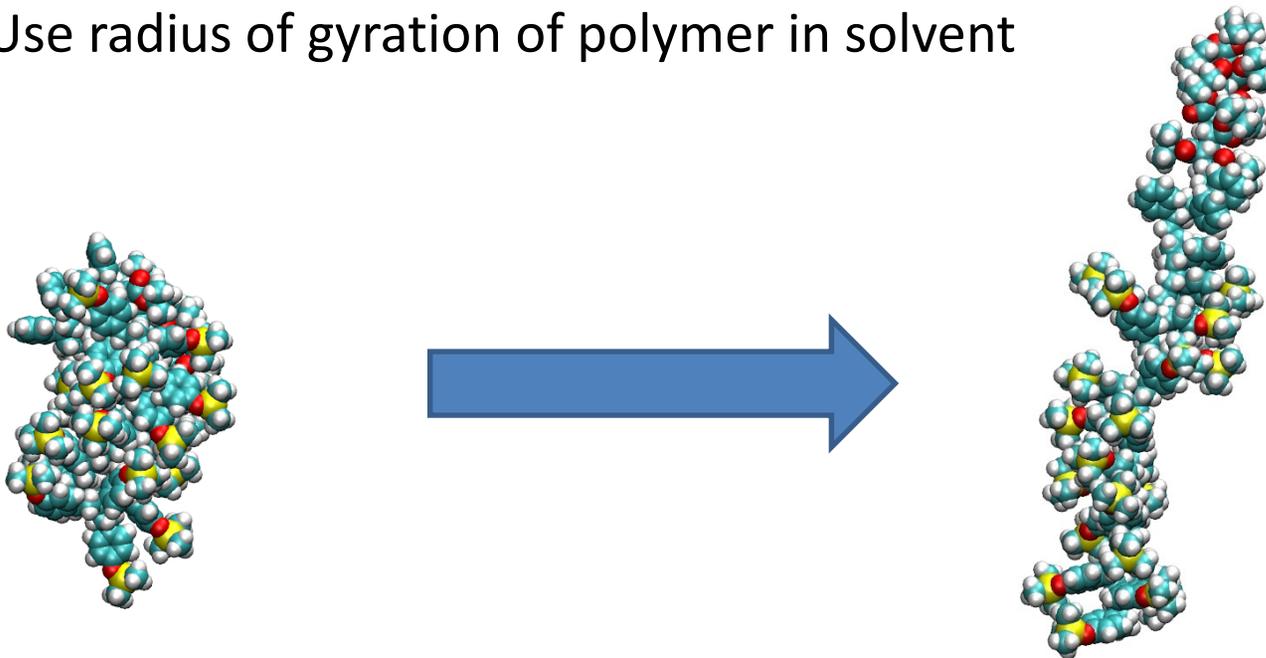
PEB: 115°C , 60 sec



ESCAP in Solution



- What is the mechanism for ESCAP dissolution?
 - Need to understand structure of polymer in solvent and film
- Steered MD
 - Forces system to go through a range of configurations
 - Provides estimate of free energy
 - Use radius of gyration of polymer in solvent



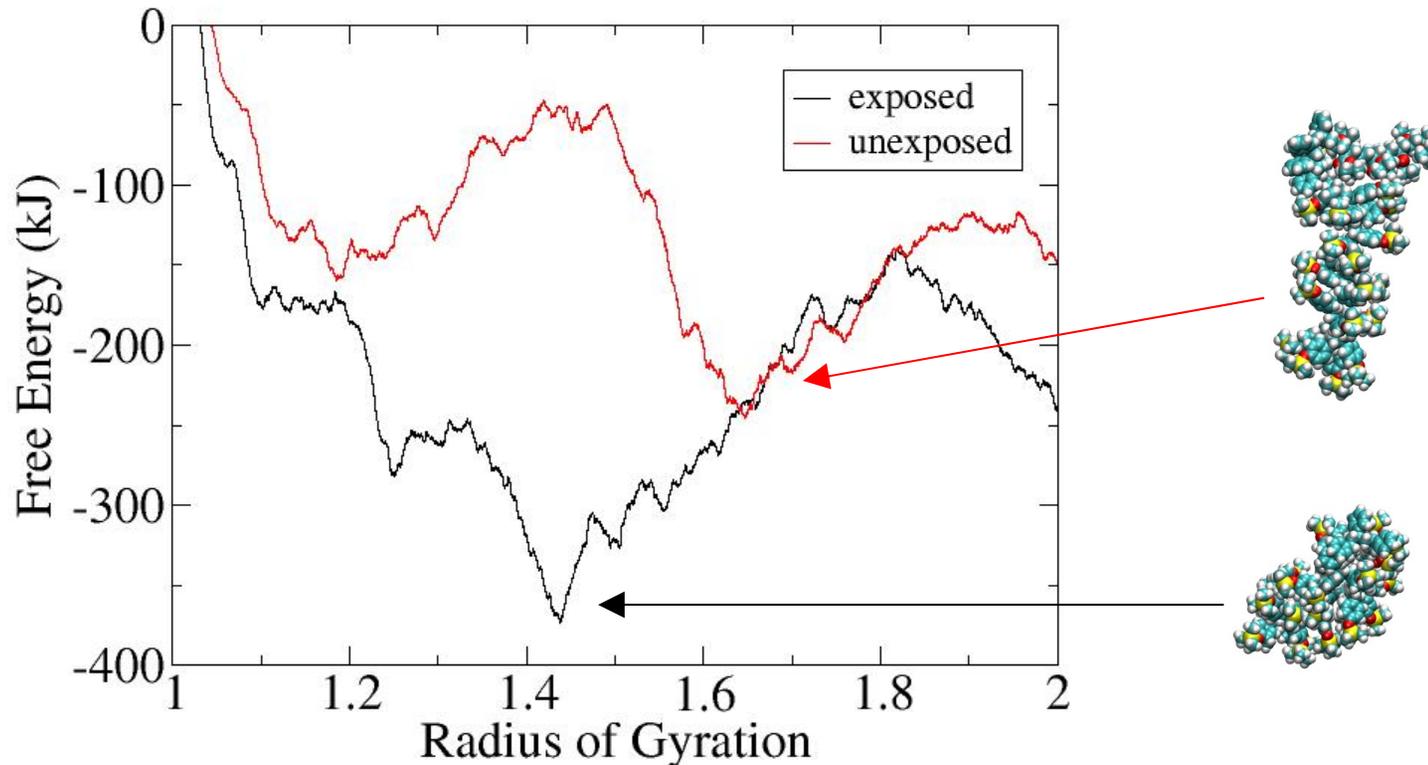


Stretching Movie





Stretching Result Curve



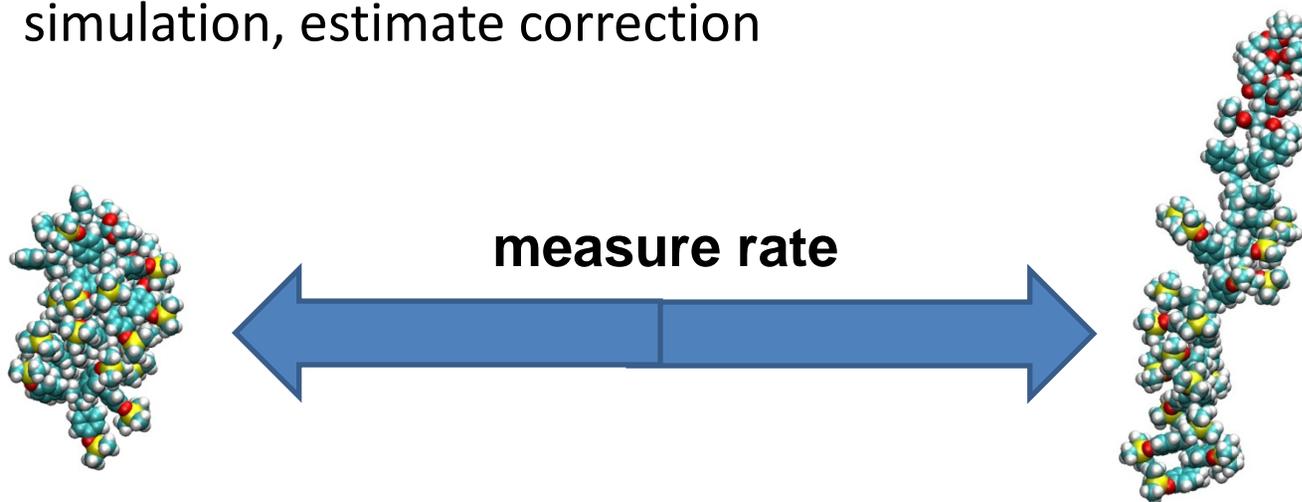
- Exposed: prefers to extend modified region while coiling
 - HMD Siloxane is borderline poor solvent
- Unexposed: prefers extended form, has meta-stable coil
 - HMD Siloxane is a good solvent, but dissolution requires exposed film surface to have correct confirmation



Flux Tempered Meta-Dynamics



- Steered MD accuracy depends on pulling rate
 - Too time consuming to get high accuracy
 - Need to refine free energy estimate with different method
- Flux Tempered Meta Dynamics (in progress)
 - Use initial estimate obtained by Steered MD
 - Bias sampling to negate current free energy estimate
 - Measure time to sample all configurations during long simulation, estimate correction





Conclusion



- Alternative solvents are promising
 - Environmentally benign
 - Help abate pattern collapse
 - Generic solutions possible
- Molecular simulation aids development
 - Screen without synthesizing
 - Develop mechanistic understanding
- Siloxane Solvents
 - Non-toxic
 - Energy efficient
 - Effective
 - Still exploring mechanistic understanding



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